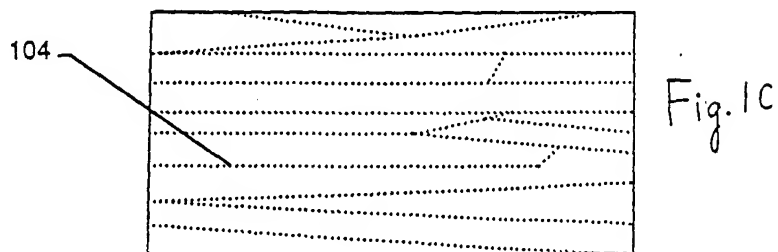
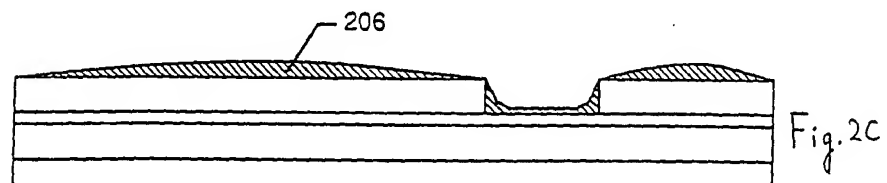
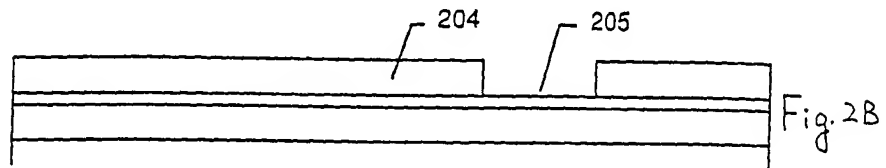
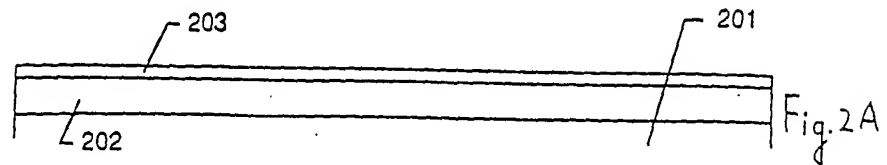


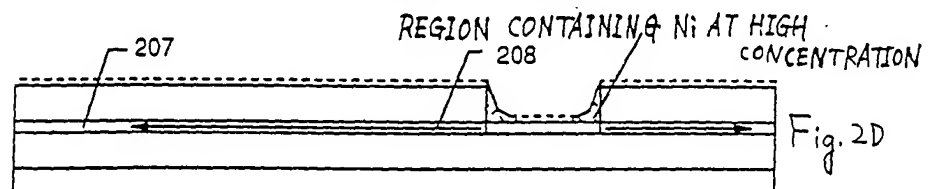
ILLUMINATION WITH  
LASER LIGHT OR STRONG LIGHT



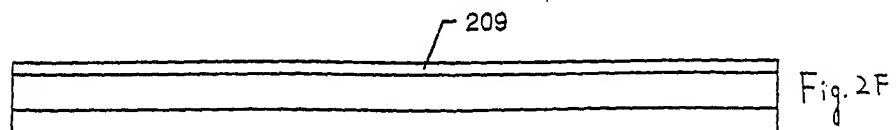
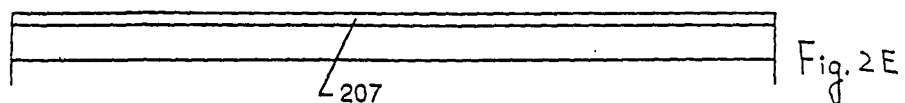
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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING  
METHOD AND SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURING METHOD

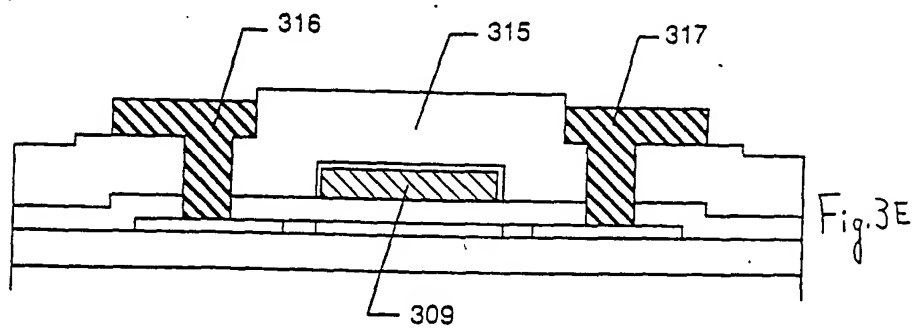
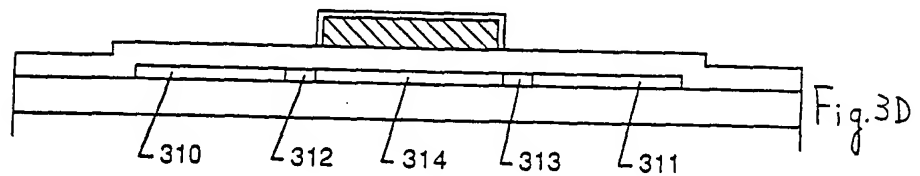
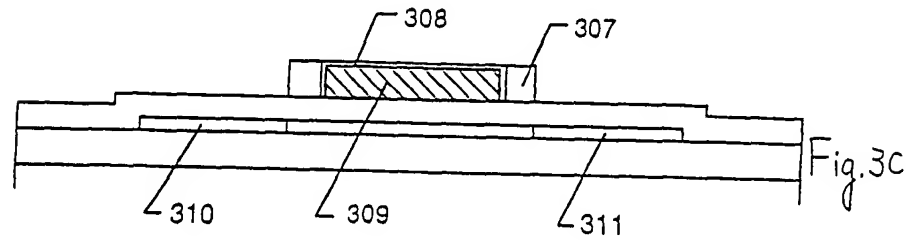
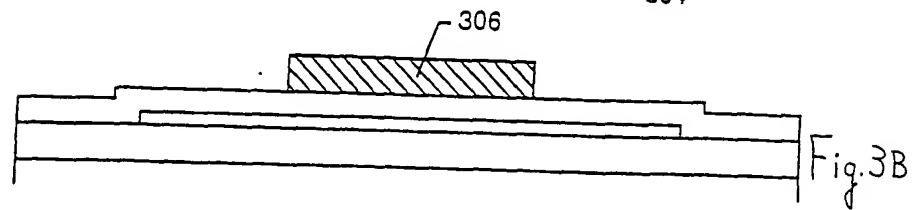
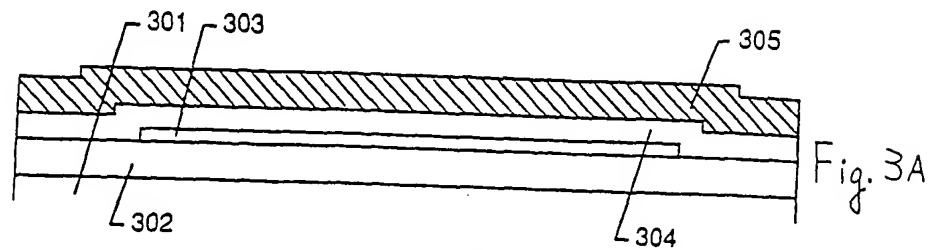
HEAT TREATMENT FOR CRYSTALLIZATION



ILLUMINATION WITH LASER LIGHT OR STRONG LIGHT



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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING  
METHOD AND SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURING METHOD

Applicant(s): S. Yamazaki et al.

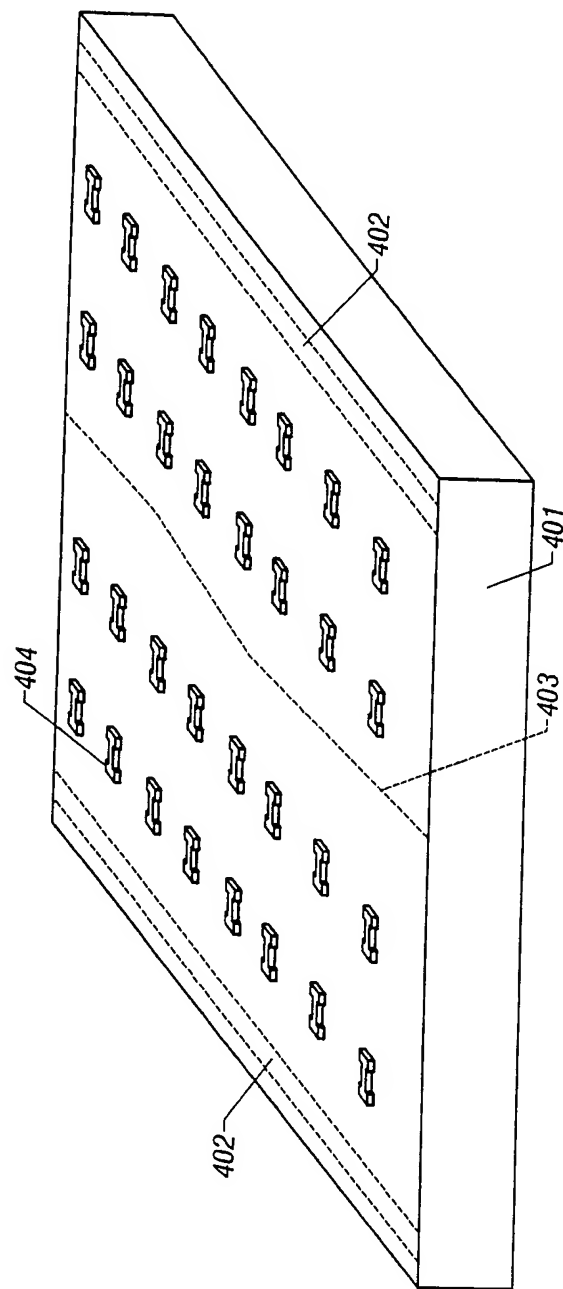
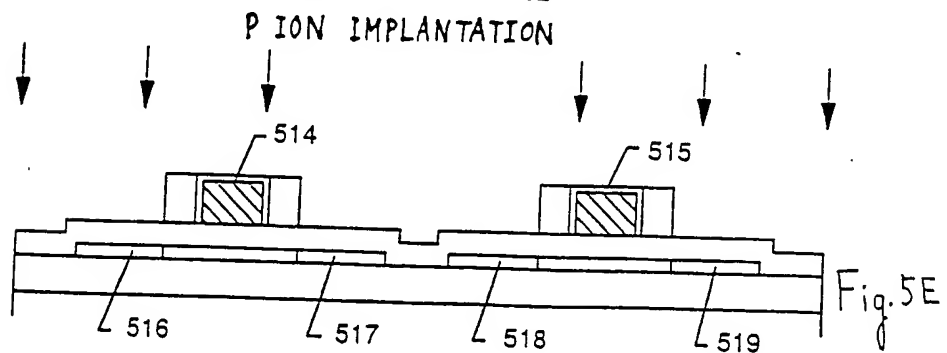
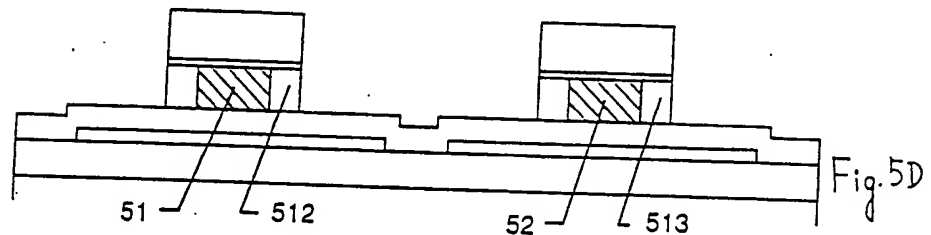
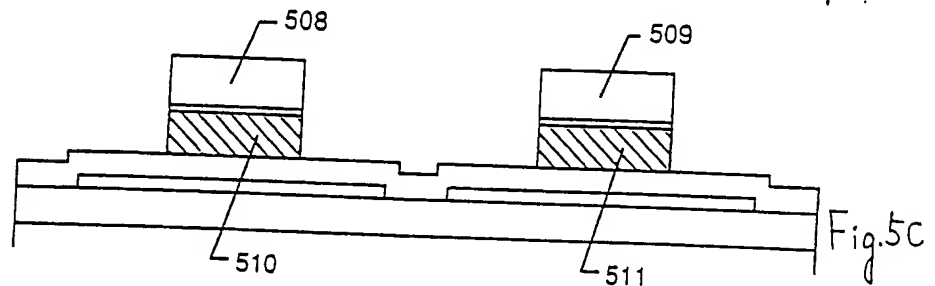
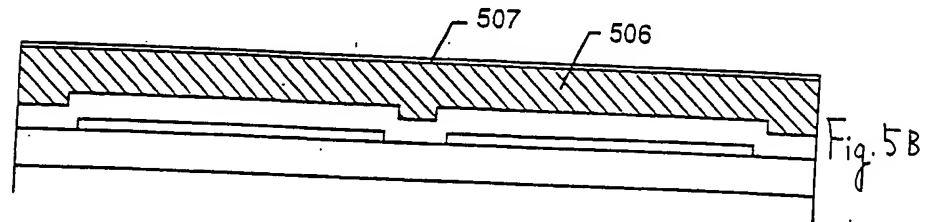
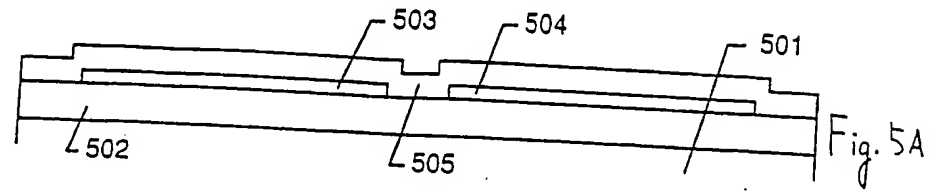
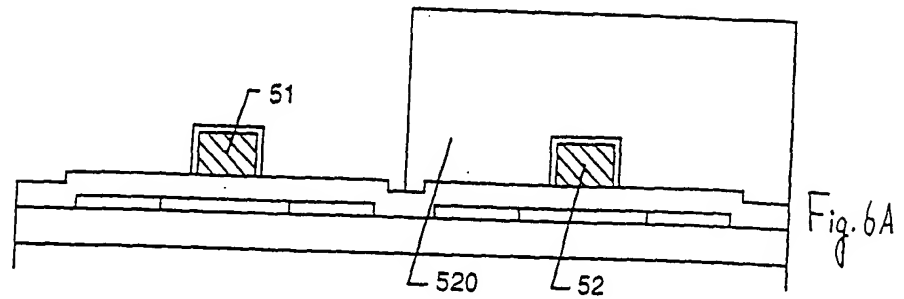
SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING  
METHOD AND SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURING METHOD

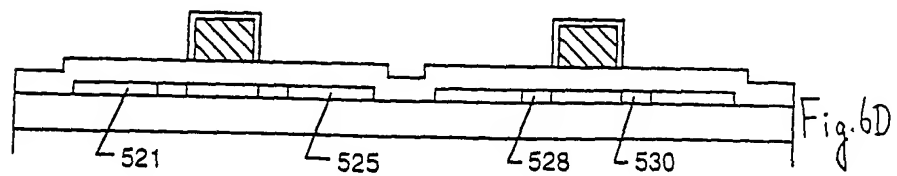
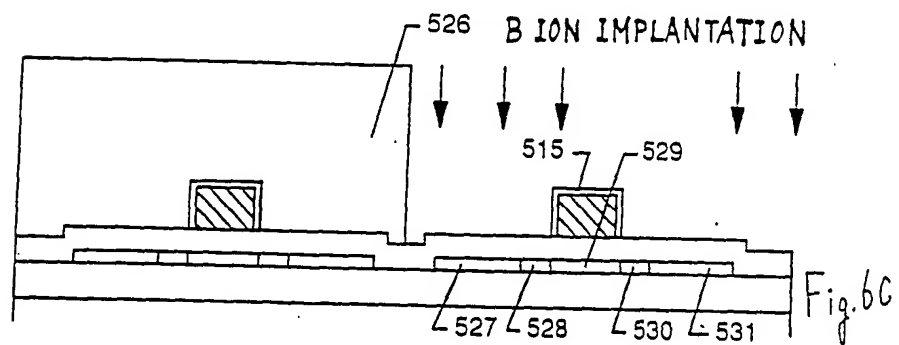
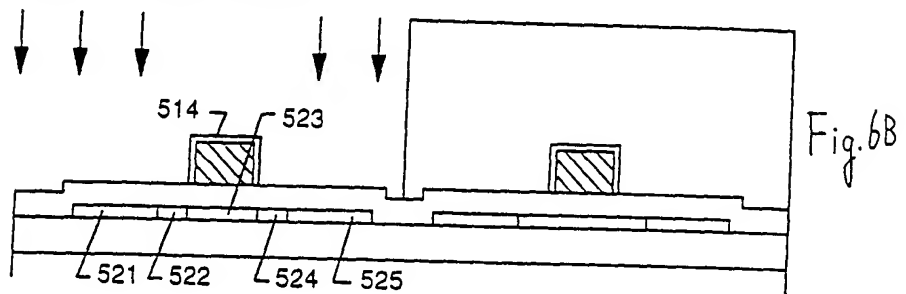
FIG. 4

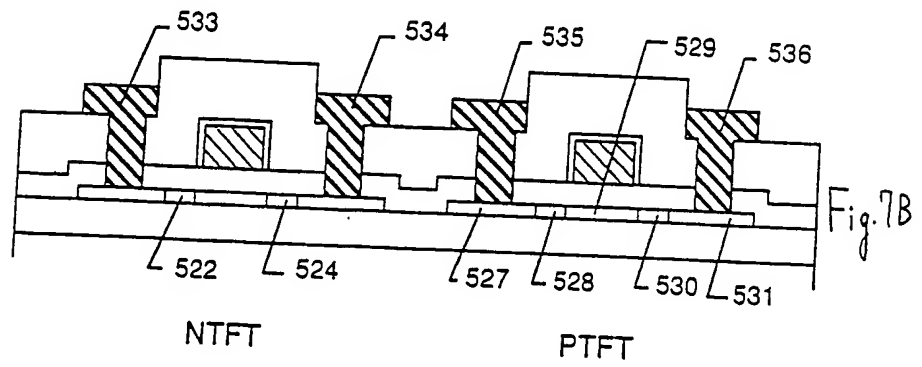
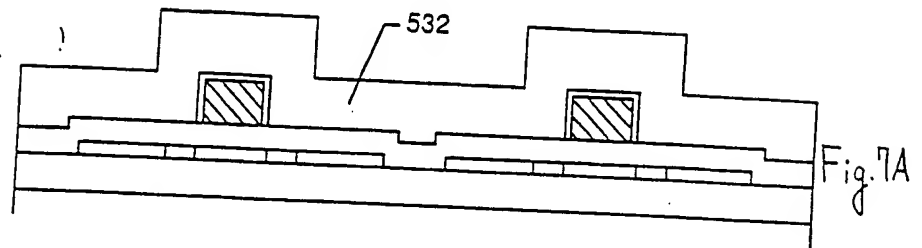


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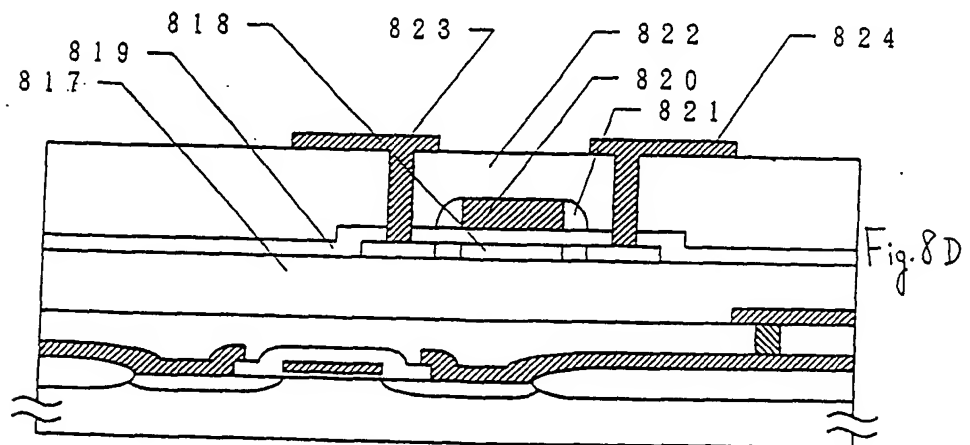
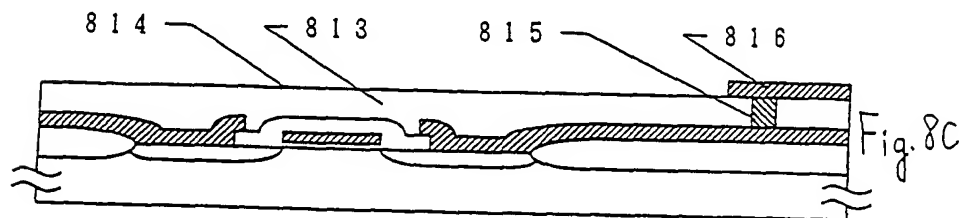
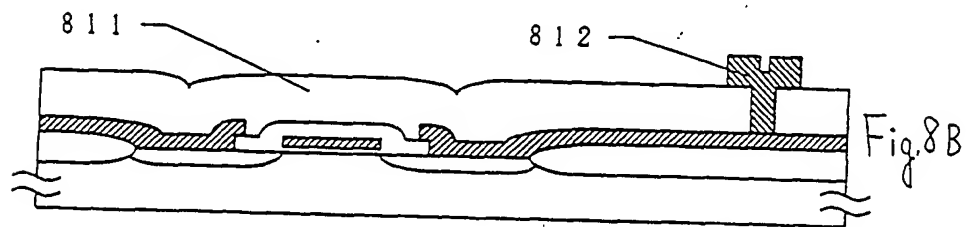
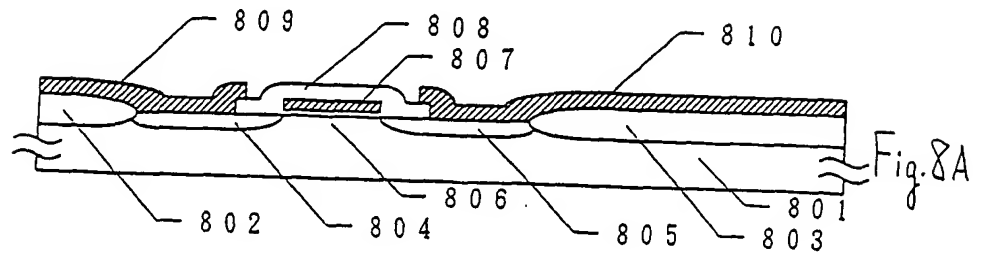
SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING  
METHOD AND SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURING METHOD

P ION IMPLANTATION



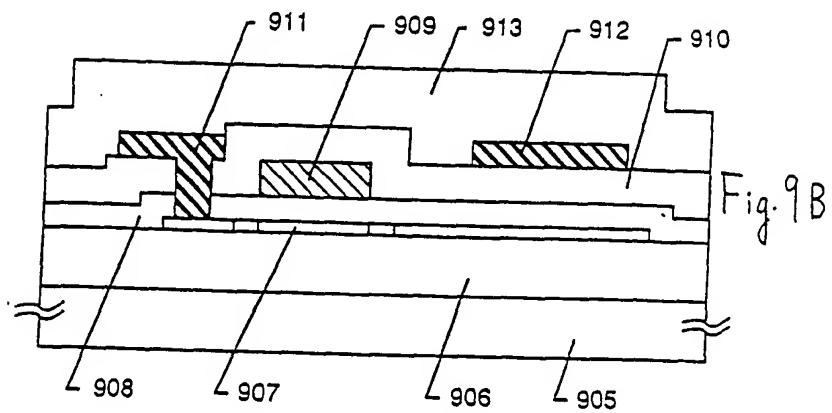
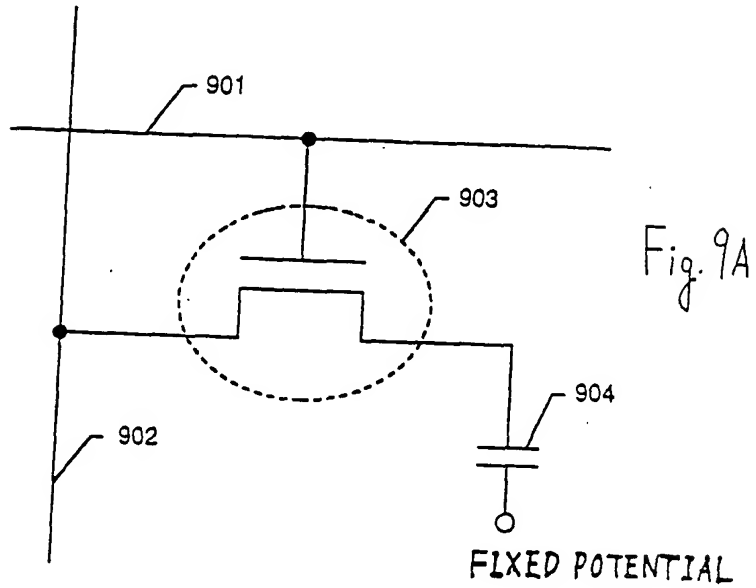


Applicant(s): S. Yamazaki et al.

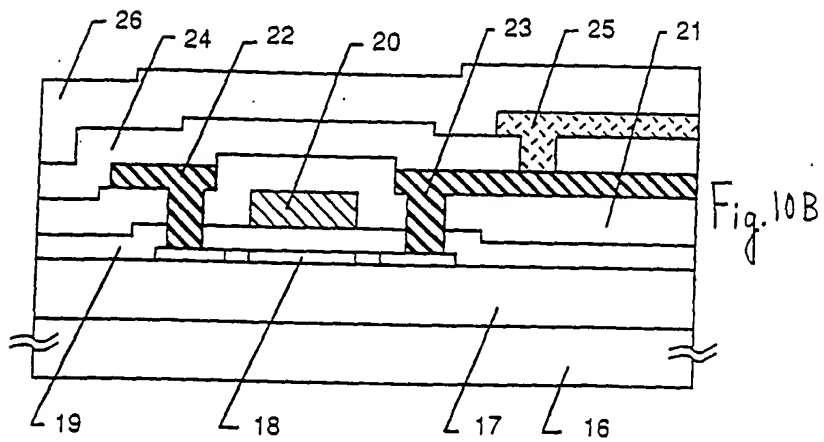
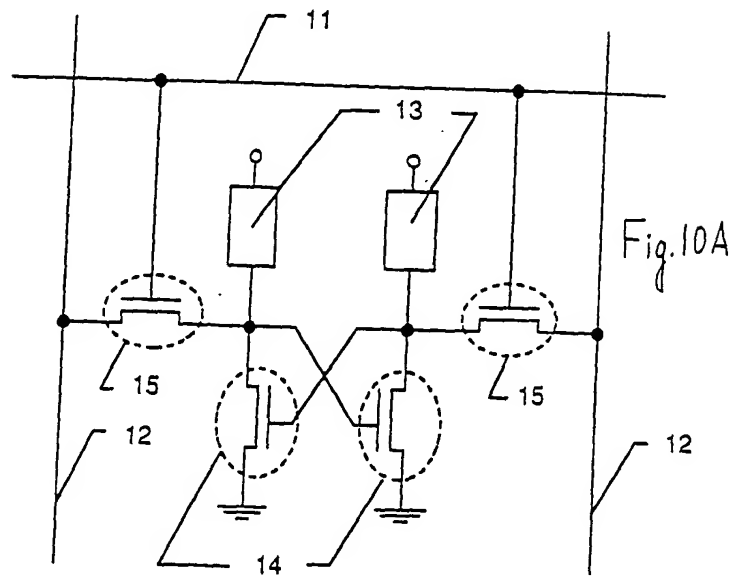
SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING  
METHOD AND SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURING METHOD

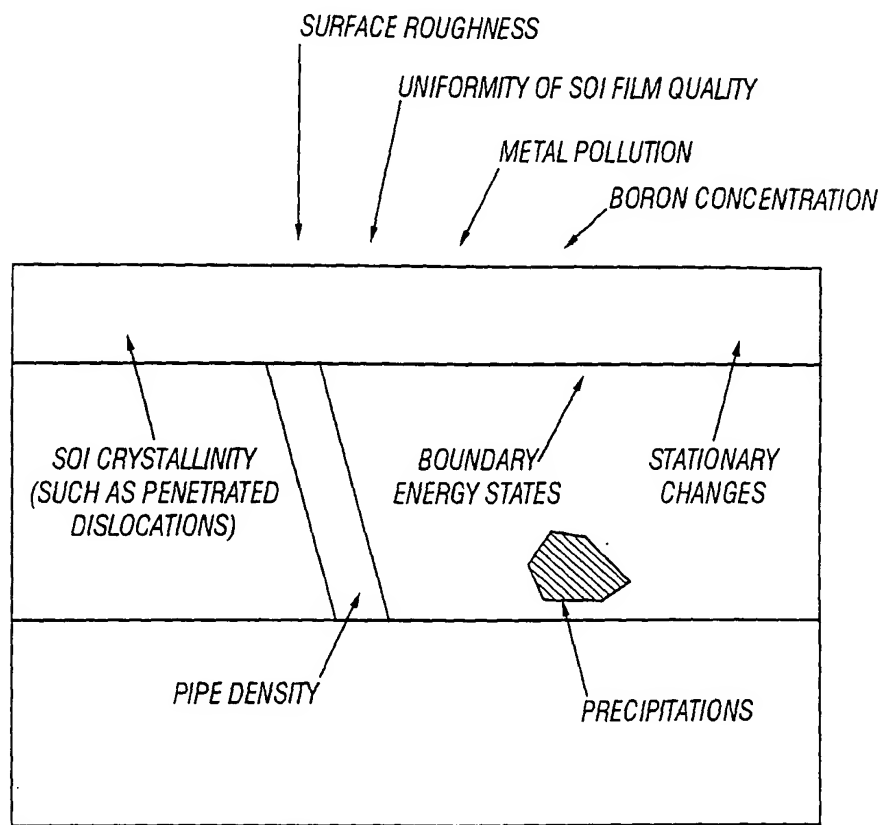


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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING  
METHOD AND SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURING METHOD

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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING  
METHOD AND SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURING METHOD

**FIG. 11**

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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING  
METHOD AND SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURING METHOD

Fig. 12

ELE- MENT	CONCENTRATION (PPM)	ELE- MENT	CONCENTRATION (PPM)
Fe	0.045	Ca	0.16
Ni	0.016	Mn	<0.001
Na	>0.005	Al	0.004
K	>0.004	U *2	<0.000031
Ti *1	<0.05	Th *2	<0.00016
Mg	>0.005	F *3	310
Cu	0.009	Cl *2	<0.73
Cr	0.003	OH *4	ND

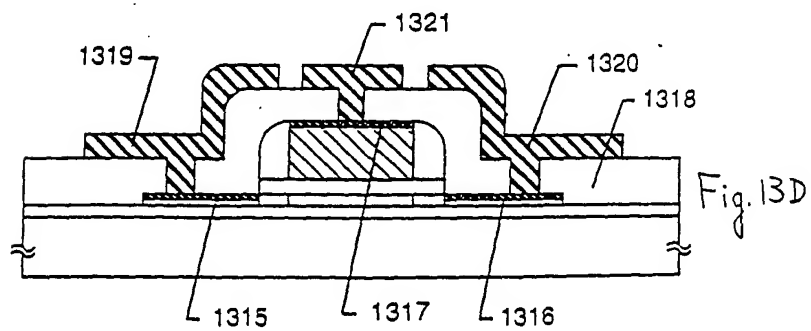
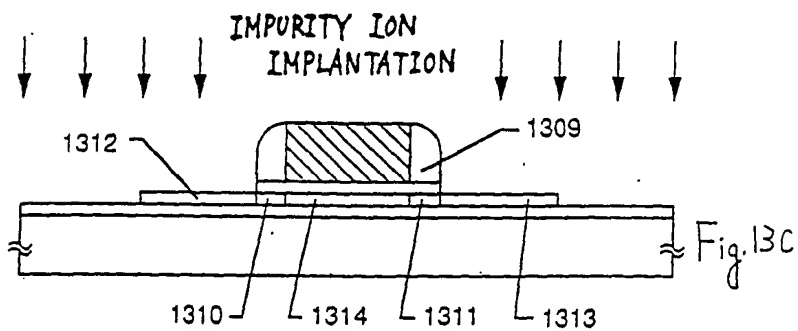
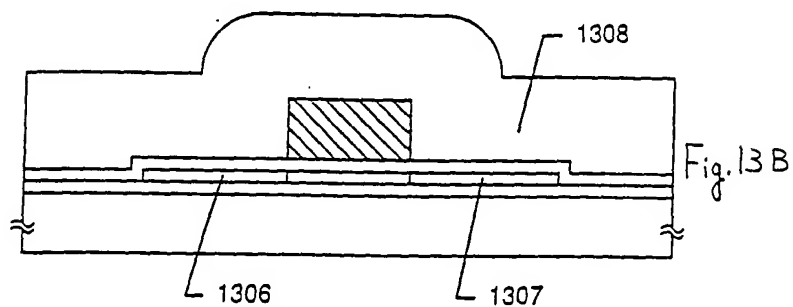
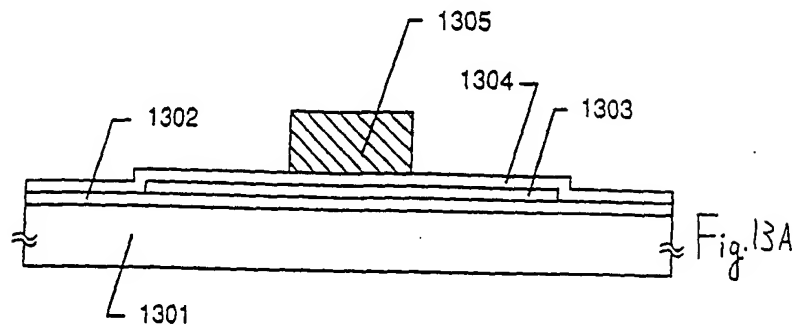
MEASUREMENT METHOD: POLARIZED ZEEMAN FLAMELESS ATOMIC  
ABSORPTION

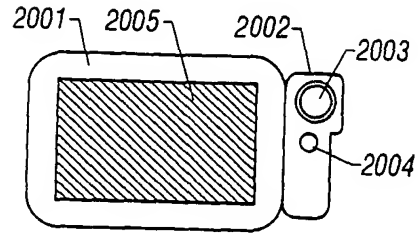
NOTES) \*1 ... ICP EMISSION ANALYSIS

\*2 ... RADIOACTIVATION ANALYSIS

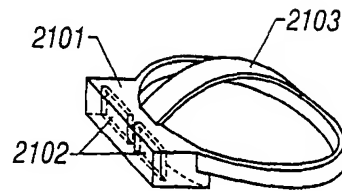
\*3 .. EPMA

\*4 ... INFRARED ABSORPTION

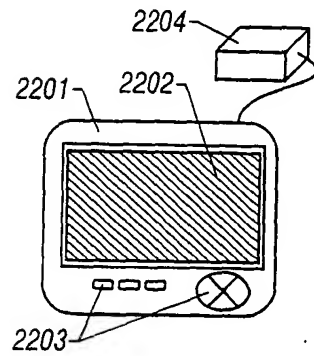




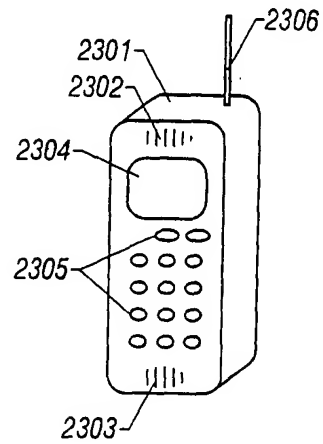
**FIG. 14A**



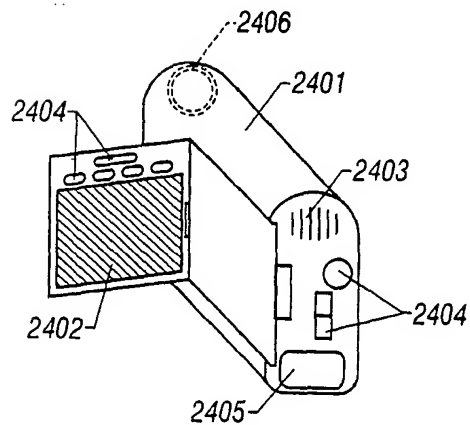
**FIG. 14B**



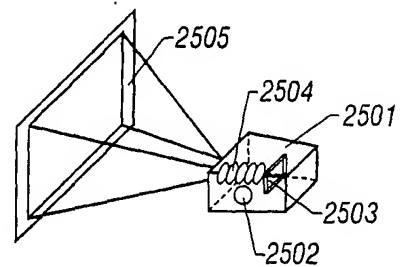
**FIG. 14C**



**FIG. 14D**



**FIG. 14E**



**FIG. 14F**